

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Samuel ANDERSON

Application No.: 10/596,720

Confirmation No.: 9904

Filed: June 22, 2006

Art Unit: 2814

For: SUPERJUNCTION DEVICE HAVING OXIDE  
LINED TRENCHES AND METHOD FOR  
MANUFACTURING A SUPERJUNCTION  
DEVICE HAVING OXIDE LINED TRENCHES

Examiner: Raj R. Gupta

**DECLARATION OF SAMUEL ANDERSON UNDER 37 C.F.R. § 1.132**

I, Samuel Anderson, hereby declare as follows:

1. I am the same Samuel Anderson who is the inventor in the above-identified patent application ("the '720 application"). I am the President and Chief Executive Officer of IceMOS Technology, Ltd., the assignee of the '720 application.

2. I received a Bachelor of Science degree in Electrical Engineering and a Master of Science degree in Physics from Queen's University Belfast in Belfast, Northern Ireland. I received a Master of Technology degree from Arizona State University.

3. In a preferred embodiment of the present invention, after sidewalls of the mesas formed by trenches in the semiconductor substrate are doped to a desired level, an oxide layer is deposited over the sidewalls and the bottoms of the trenches in a thickness of between about 100 Ångstroms to 10,000 Ångstroms.

4. By controlling the thickness of the oxide layer within this range, one is able to control the capacitance of the device such that the properties of the superjunction device may be maintained while voltage loss is minimized.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are

punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Nov 5 2010  
(Date)

  
Samuel Anderson